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(71) Applicant *(for all designated States except US)*: **MICRON TECHNOLOGY, INC.** [US/US]; 8000 South Federal Way, (a Corporation Of The State Of Delaware), Boise, ID 83716 (US).

(72) Inventors; and
(75) Inventors/Applicants *(for US only)*: **QIN, Shu** [US/US]; 4141 Nez Perce St. Apt. 117, Boise, ID 83705 (US). **ZHANG, Ming** [CN/US]; 2106 Ridgeview Way, Boise, ID 83712 (US).

(74) Agents: **MATKIN, Mark S.** et al.; Wells St. John P.S., 601 West First Avenue, Suite 1300, Spokane, WA 99201 (US).

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(54) Title: METHODS OF PROCESSING UNITS COMPRISING CRYSTALLINE MATERIALS, AND METHODS OF FORMING SEMICONDUCTOR-ON INSULATOR CONSTRUCTIONS

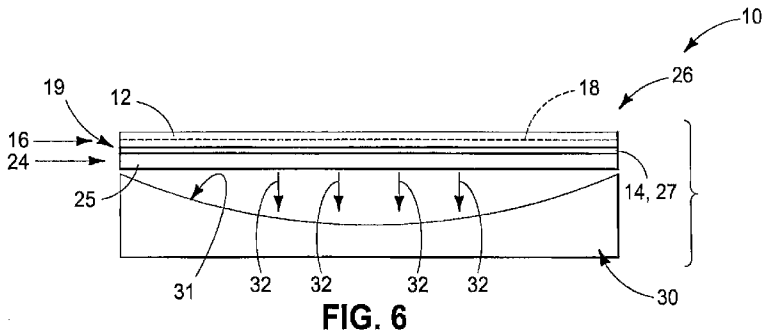


FIG. 6

(57) Abstract: Some embodiments include methods of processing a unit containing crystalline material. A damage region may be formed within the crystalline material, and a portion of the unit may be above the damage region. A chuck may be used to bend the unit and thereby induce cleavage along the damage region to form a structure from the portion of the unit above the damage region. Some embodiments include methods of forming semiconductor-on-insulator constructions. A unit may be formed to have dielectric material over monocrystalline semiconductor material. A damage region may be formed within the monocrystalline semiconductor material, and a portion of the monocrystalline semiconductor material may be between the damage region and the dielectric material. The unit may be incorporated into an assembly with a handle component, and a chuck may be used to contort the assembly and thereby induce cleavage along the damage region.

WO 2013/052236 A1